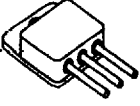
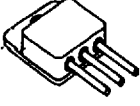


NEW ENGLAND SEMICONDUCTOR

**BIPOLAR
POWER TRANSISTOR
NPN PLANAR**

PACKAGE	DEVICE TYPE	BV_{CEO} VOLTS	PEAK I_C AMPS	h_{FE} min/max	$I_C @ V_{CE}$ A V	$V_{CE(sat)}$ max VOLTS	$I_C @ I_B$ A A
NPN TO-258 	NSP4865	80	90.0	10-40	70.0/5.0	2.2	70.0/7.0
	NSP4866	120	90.0	10-40	70.0/5.0	2.2	70.0/7.0
	NSP5250	100	90.0	10-40	70.0/5.0	2.2	70.0/7.0
	NSP5251	150	90.0	10-40	70.0/5.0	2.2	70.0/7.0
	NSP0100	100	100.0	20-100	60.0/4.0	0.75	60.0/6.0
	NSP0101	150	75.0	20-100	40.0/4.0	0.75	40.0/4.0
	NSP0102	200	50.0	20-100	20.0/4.0	0.75	20.0/2.0

PNP PLANAR

PNP TO-258 	NSP0200	100	75.0	10-40	50.0/5.0	1.0	50.0/5.0
	NSP0201	80	75.0	10-40	50.0/5.0	1.0	50.0/5.0
	NSP0202	60	75.0	15-30	50.0/5.0	1.0	50.0/5.0
	NSP0203	100	100.0	15-100	60.0/4.0	1.0	60.0/6.0
	NSP0204	150	75.0	15-100	40.0/4.0	1.0	40.0/4.0

- Electrical Characteristics at 25° C unless otherwise noted
- ^Available in JAN, JANTX, JANTXV